

VCXO-TO-LVCMOS/LVTTL OUTPUT

ICS8105251

GENERAL DESCRIPTION



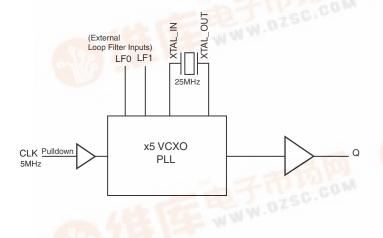
The ICS810525I is a high performance, low jitter/low phase noise VCXO from IDT. The ICS810525I works in conjunction with a 25MHz pullable crystal to generate an LVCMOS/LVTTL output clock of 25MHz from an input clock of

5MHz. The frequency of the VCXO is adjusted by the VC control voltage input. The output range is ±100ppm around the nominal crystal frequency. The LF1 control voltage range is 0 - V_{no}. The device is packaged in a small 16 TSSOP package and is ideal for use on space constrained boards.

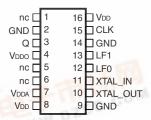
FEATURES

- One single-ended LVCMOS/LVTTL output
- One single-ended clock accepts the following input types: LVCMOS, LVTTL
- Accepts input frequency of 5MHz
- Absolute pull range: 100ppm
- Proprietary multiplier provides low jitter, high frequency output
- RMS phase jitter @ 25MHz, using a 25MHz crystal (1kHz - 1MHz): 0.27ps (typical)
- Full 3.3V supply, or 3.3V core/2.5V output supply
- -40°C to 85°C ambient operating temperature
- WWW.DZSC.COM Available in lead-free (RoHS 6) package

BLOCK DIAGRAM



PIN ASSIGNMENT



ICS810525I

16-Lead TSSOP

4.4mm x 5.0mm x 0.925mm package body G Package Top View

TABLE 1. PIN DESCRIPTIONS

| Number | Name | Тур | е | Description |
|-----------|------------------------------|------------------------|----------|--|
| 1, 5, 6 | nc | Unused | | No connect. |
| 2, 9, 14 | GND | Power | | Power supply ground. |
| 3 | Ø | Output | | Single-ended clock output. LVCMOS/LVTTL interface levels. |
| 4 | $V_{\scriptscriptstyle DDO}$ | Power | | Output power supply pin. |
| 7 | $V_{\scriptscriptstyle DDA}$ | Power | | Analog supply pin. |
| 8, 16 | $V_{_{\mathrm{DD}}}$ | Power | | Core power supply pins. |
| 10, 11 | XTAL_OUT, XTAL_IN | Input | | VCXO crystal oscillator interface. XTAL_IN is the input. XTAL_OUT is the output. |
| 12, 13 | LF0, LF1 | Analog Input/Output | | Loop filter connection node pins. |
| 15 | CLK | Input | Pulldown | Single-ended clock input. LVCMOS/LVTTL interface levels. |

NOTE: Pulldown refers to internal input resistors. See Table 2, Pin Characteristics, for typical values.

TABLE 2. PIN CHARACTERISTICS

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|-----------------------|-------------------------------|---------------------------|---------|---------|---------|-------|
| C _{IN} | Input Capacitance | | | 4 | | pF |
| C _{PD} | Power Dissipation Capacitance | V _{DDO} = 3.465V | | 8 | | pF |
| | | $V_{DDO} = 2.625V$ | | 5 | | pF |
| R _{PULLDOWN} | Input Pulldown Resistor | | | 51 | | kΩ |
| R _{OUT} | Output Impedance | $V_{DDO} = 3.3V$ | | 15 | | Ω |
| | | V _{DDO} = 2.5V | | 20 | | Ω |

VCXO-TO-LVCMOS/LVTTL OUTPUT

查询"810525AGILF"供应商

ABSOLUTE MAXIMUM RATINGS

Supply Voltage, V_{DD} 4.6V

Inputs, V_{I} -0.5V to V_{DD} + 0.5 V

Outputs, V_{O} -0.5V to V_{DDO} + 0.5V

Package Thermal Impedance, θ_{JA} 92.4°C/W (0 mps)

Storage Temperature, T_{STG} -65°C to 150°C

NOTE: Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

Table 3A. Power Supply DC Characteristics, $V_{DD} = V_{DDO} = 3.3V \pm 5\%$, Ta = -40°C to 85°C

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|------------------|-----------------------|-----------------|------------------------|---------|-----------------|-------|
| V _{DD} | Power Supply Voltage | | 3.135 | 3.3 | 3.465 | V |
| V _{DDA} | Analog Supply Voltage | | V _{DD} - 0.05 | 3.3 | V _{DD} | V |
| V _{DDO} | Output Supply Voltage | | 3.135 | 3.3 | 3.465 | V |
| I _{DD} | Power Supply Current | | | | 35 | mA |
| I _{DDA} | Analog Supply Current | | | | 5 | mA |

Table 3B. Power Supply DC Characteristics, $V_{DD} = 3.3V \pm 5\%$, $V_{DDO} = 2.5V \pm 5\%$, Ta = -40°C to 85°C

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|------------------|-----------------------|-----------------|------------------------|---------|-----------------|-------|
| V _{DD} | Core Supply Voltage | | 3.135 | 3.3 | 3.465 | V |
| V _{DDA} | Analog Supply Voltage | | V _{DD} - 0.05 | 3.3 | V _{DD} | V |
| V _{DDO} | Output Supply Voltage | | 2.375 | 2.5 | 2.625 | V |
| I _{DD} | Power Supply Current | | | | 35 | mA |
| I _{DDA} | Analog Supply Current | | | | 5 | mA |

Table 3C. LVCMOS/LVTTL DC Characteristics, $V_{DD} = 3.3V \pm 5\%$, $V_{DDO} = 3.3V \pm 5\%$ or $2.5V \pm 5\%$, Ta = -40°C to 85° C

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|-----------------|---------------------------------------|--|---------|---------|-----------------------|-------|
| V _{IH} | Input High Voltage | | 2 | | V _{DD} + 0.3 | V |
| V _{IL} | Input Low Voltage | | -0.3 | | 0.8 | V |
| V_{LF1} | VCXO Control Voltage | | 0 | | V _{DD} | V |
| I _{IH} | Input High Current | $V_{DD} = V_{IN} = 3.465V \text{ or } 2.625V$ | | | 150 | μΑ |
| I | Input Low Current | $V_{DD} = 3.465V \text{ or } 2.625V, V_{IN} = 0V$ | -5 | | | μΑ |
| I _i | Input Current of V _{LF1} pin | $V_{DD} = 3.465V \text{ or } 2.625V$ | -100 | | 100 | μΑ |
| V | Output High Voltage | $V_{DDO} = 3.3V \pm 5\%, I_{OH} = -12mA$ | 2.6 | | | V |
| V _{OH} | Output High Voltage | $V_{DDO} = 2.5V \pm 5\%, I_{OH} = -12mA$ | 1.8 | | | V |
| V _{OL} | Output Low Voltage | $V_{DDO} = 3.3V \text{ or } 2.5V \pm 5\% \ I_{OL} = 12\text{mA}$ | | | 0.5 | V |

Table 4A. AC Characteristics, $V_{DD} = V_{DDO} = 3.3V \pm 5\%$, Ta = -40°C to 85°C

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|---------------------------------|--------------------------------------|-----------------------------------|---------|---------|---------|-------|
| f _{out} | Output Frequency | | | | 25 | MHz |
| <i>t</i> jit(Ø) | RMS Phase Jitter (Random); NOTE 1 | Integration Range: 1kHz – 1MHz | | 0.27 | | ps |
| t _R / t _F | Output Rise/Fall Time | 20% to 80% | 500 | | 1200 | ps |
| odc | Output Duty Cycle | | 48 | | 52 | % |

NOTE: Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfpm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

Characterized using a 3kHz bandwidth filter.

NOTE 1: Please refer to the Phase Noise Plot.

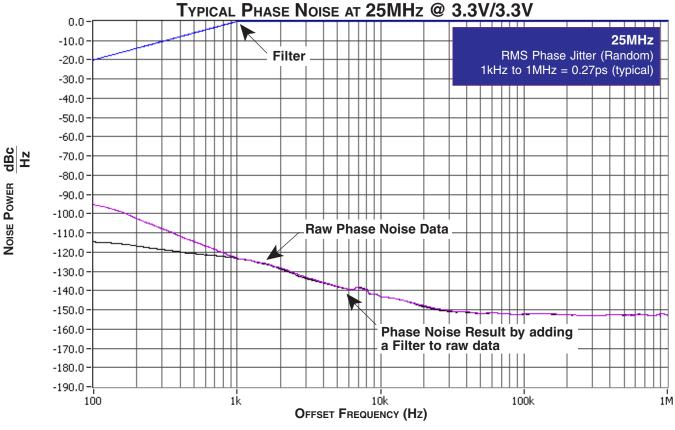
Table 4B. AC Characteristics, $V_{DD} = 3.3V \pm 5\%$, $V_{DDO} = 2.5V \pm 5\%$, Ta = -40°C to 85°C

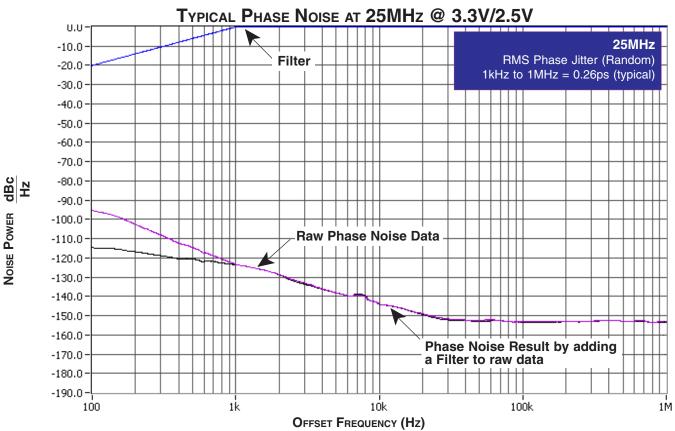
| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|---------------------------------|--------------------------------------|-----------------------------------|---------|---------|---------|-------|
| f _{out} | Output Frequency | | | | 25 | MHz |
| tjit(Ø) | RMS Phase Jitter (Random); NOTE 1 | Integration Range: 1kHz – 1MHz | | 0.26 | | ps |
| t _R / t _F | Output Rise/Fall Time | 20% to 80% | 600 | | 2100 | ps |
| odc | Output Duty Cycle | | 44 | | 56 | % |

NOTE: Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfpm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

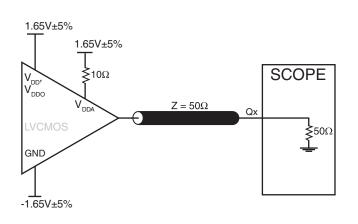
Characterized using a 3kHz bandwidth filter.

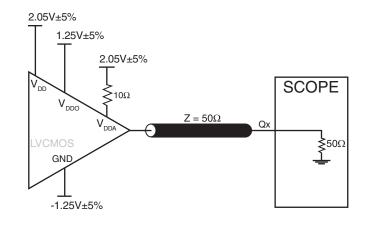
NOTE 1: Please refer to the Phase Noise Plot.





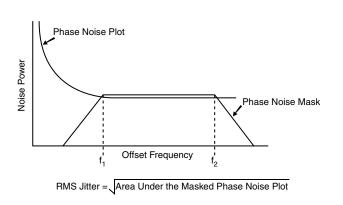
PARAMETER MEASUREMENT INFORMATION



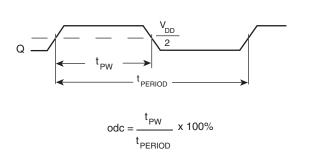


3.3V CORE/3.3V OUTPUT LOAD AC TEST CIRCUIT



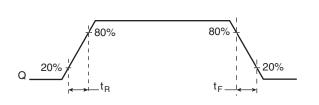


3.3V CORE/2.5V OUTPUT LOAD AC TEST CIRCUIT



RMS PHASE JITTER





OUTPUT RISE/FALL TIME

APPLICATION INFORMATION

SCHEMATIC EXAMPLE

Figure 1 shows an example of the ICS810525I application schematic. In this example, the device is operated at $V_{DD} = 3.3V$. The decoupling capacitors should be located as close as possible to the power pin. The input is driven by a 3.3V LVCMOS

driver. A 2-pole filter loop filter with Low LBW setting is used in this example. It is recommended to refer to the ICS810525I datasheet for more detail on loop filter values.

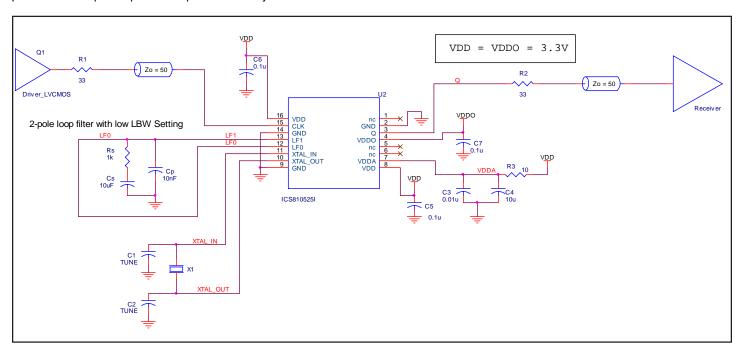


FIGURE 1. ICS810525I SCHEMATIC EXAMPLE

VCXO-PLL EXTERNAL COMPONENTS

Choosing the correct external components and having a proper printed circuit board (PCB) layout is a key task for quality operation of the VCXO-PLL. In choosing a crystal, special precaution must be taken with the package and load capacitance (C₁). In addition, frequency, accuracy and temperature range must also be considered. Since the pulling range of a crystal also varies with the package, it is recommended that a metal-canned package like HC49 be used. Generally, a metal-canned package has a larger pulling range than a surface mounted device (SMD). For crystal selection information, refer to the VCXO Crystal Selection Application Note.

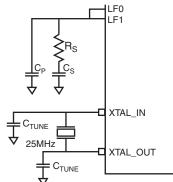
The crystal's load capacitance $C_{\scriptscriptstyle L}$ characteristic determines its resonating frequency and is closely related to the VCXO tuning range. The total external capacitance seen by the crystal when installed on a board is the sum of the stray board capacitance, IC package lead capacitance, internal varactor capacitance and any installed tuning capacitors ($C_{\scriptscriptstyle \rm TIMF}$).

If the crystal's $C_{\scriptscriptstyle L}$ is greater than the total external capacitance, the VCXO will oscillate at a higher frequency than the crystal specification. If the crystal's $C_{\scriptscriptstyle L}$ is lower than the total external capacitance, the VCXO will oscillate at a lower frequency than

the crystal specification. In either case, the absolute tuning range is reduced. The correct value of $C_{\scriptscriptstyle L}$ is dependent on the characteristics of the VCXO. The recommended $C_{\scriptscriptstyle L}$ in the Crystal Parameter Table balances the tuning range by centering the tuning curve.

The VCXO-PLL Loop Bandwidth Selection Table shows $R_{\rm s}$, $C_{\rm s}$ and $C_{\rm p}$ values for recommended high, mid and low loop bandwidth configurations. The device has been characterized using these parameters. For other configurations, refer to the Loop Filter Component Selection for VCXO Based PLLs Application Note.

The crystal and external loop filter components should be kept as close as possible to the device. Loop filter and crystal traces should be kept short and separated from each other. Other signal traces should be kept separate and not run underneath the device, loop filter or crystal components.



VCXO CHARACTERISTICS TABLE

| Symbol | ymbol Parameter | | Unit |
|---------------------|---------------------------|------|-------|
| k _{vcxo} | VCXO Gain | 15 | kHz/V |
| C _{v_Low} | Low Varactor Capacitance | 9.8 | pF |
| C _{v_HIGH} | High Varactor Capacitance | 22.7 | pF |

VCXO-PLL APPROXIMATE LOOP BANDWIDTH SELECTION TABLE

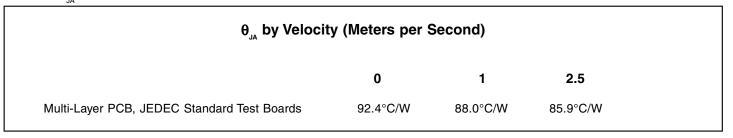
| Bandwidth | Crystal Frequency (MHz) | $R_{s}(k\Omega)$ | C _s (µF) | C _P (pF) |
|--------------|-------------------------|------------------|---------------------|---------------------|
| 125Hz (Low) | 25MHz | 1 | 10 | 10000 |
| 1.5kHz (Mid) | 25MHz | 12 | 0.1 | 100 |
| 3kHz (High) | 25MHz | 25 | 0.1 | 100 |

CRYSTAL CHARACTERISTICS

| Symbol | Parameter | Minimum | Typical | Maximum | Units |
|--------------------------------|------------------------------|---------|----------|-------------|-------|
| | Mode of Operation | | Fundamer | ntal | |
| f _N | Frequency | | 25 | | MHz |
| f _T | Frequency Tolerance | | | ±20 | ppm |
| f _s | Frequency Stability | | | ±20 | ppm |
| | Operating Temperature Range | -40 | | 85 | °C |
| C _L | Load Capacitance | | 10 | | рF |
| C _o | Shunt Capacitance | | 4 | | pF |
| C _o /C ₁ | Pullability Ratio | | 220 | 240 | |
| ESR | Equivalent Series Resistance | | | 40 | Ω |
| | Drive Level | | | 1 | mW |
| | Aging @ 25°C | | | ±3 per year | ppm |

RELIABILITY INFORMATION

Table 5. $\boldsymbol{\theta}_{_{\mathrm{IA}}} \text{vs. Air Flow Table for 16 Lead TSSOP}$



TRANSISTOR COUNT

The transistor count for ICS810525I is: 635

PACKAGE OUTLINE & PACKAGE DIMENSIONS

PACKAGE OUTLINE - G SUFFIX FOR 16 LEAD TSSOP

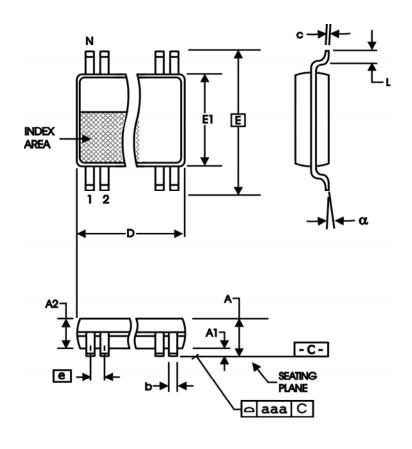


TABLE 6. PACKAGE DIMENSIONS

| | Millim | neters |
|--------|---------|---------|
| SYMBOL | Minimum | Maximum |
| N | 1 | 6 |
| А | | 1.20 |
| A1 | 0.05 | 0.15 |
| A2 | 0.80 | 1.05 |
| b | 0.19 | 0.30 |
| С | 0.09 | 0.20 |
| D | 4.90 | 5.10 |
| Е | 6.40 E | BASIC |
| E1 | 4.30 | 4.50 |
| е | 0.65 E | BASIC |
| L | 0.45 | 0.75 |
| α | 0° | 8° |
| aaa | | 0.10 |

Reference Document: JEDEC Publication 95, MO-153

ICS810525I VCXO-TO-LVCMOS/LVTTL OUTPUT

查询"810525AGILF"供应商

TABLE 7. ORDERING INFORMATION

| Part/Order Number | Marking | Package | Shipping Packaging | Temperature |
|-------------------|----------|---------------------------|--------------------|---------------|
| 810525AGILF | 10525AIL | 16 Lead "Lead-Free" TSSOP | tube | -40°C to 85°C |
| 810525AGILFT | 10525AIL | 16 Lead "Lead-Free" TSSOP | 2500 tape & reel | -40°C to 85°C |

NOTE: Parts that are ordered with an "LF" suffix to the part number are the Pb-Free configuration and are RoHS compliant.

While the information presented herein has been checked for both accuracy and reliability, Integrated Device Technology, Incorporated (IDT) assumes no responsibility for either its use or for infringement of any patients or other rights of third parties, which would result from its use. No other circuits, patients, or licenses are implied. This product is intended for use in normal commercial and industrial applications. Any other applications such as those requiring high reliability or other extraordinary environmental requirements are not recommended without additional processing by IDT. IDT reserves the right to change any circuitry or specifications without notice. IDT does not authorize or warrant any IDT product for use in life support devices or critical medical instruments.

ICS810525I

VCXO-TO-LVCMOS/LVTTL OUTPUT

查询"810525AGILF"供应商

| REVISION HISTORY SHEET | | | | |
|------------------------|-------|------|--|---------|
| Rev | Table | Page | Description of Change | Date |
| В | T3C | 3 | LVCMOS DC Characteristics - added to V _{OH} /V _{OL} test conditions. | 2/24/09 |
| | | | | |

Innovate with IDT and accelerate your future networks. Contact:

www.IDT.com

For Sales

800-345-7015 (inside USA) +408-284-8200 (outside USA) Fax: 408-284-2775 www.IDT.com/go/contactIDT

For Tech Support

netcom@idt.com +480-763-2056

Corporate Headquarters

Integrated Device Technology, Inc. 6024 Silver Creek Valley Road San Jose, CA 95138 United States 800-345-7015 (inside USA) +408-284-8200 (outside USA)

